

# Enhancing SOI Waveguide Nonlinearities via Microring Resonators

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**Abstract:** All-optical devices can exploit a suite of nonlinearities in silicon photonics. We study how microring resonators (MRRs) harness these nonlinearities, with theoretical model and experimental validation. Free-carrier effects will practically always dominate Kerr in MRRs. © 2019 The Author(s)

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## 1. Introduction

Microring resonators (MRRs) are ubiquitously used in silicon photonic integrated circuits (PICs) in a variety of devices: modulators, filters, and multiplexers. Recent improvements in fabrication and packaging of silicon PICs are decreasing coupling- and waveguide loss. This allows the cavity energy inside each resonator to easily reach levels that trigger optical nonlinearities, such as Kerr effect and two-photon absorption [1]. These effects can be exploited to engineer devices for all-optical switching [2], thresholding [3] or self-pulsations [4].

All nonlinear optical effects in single waveguides must be taken into account to correctly model the experimental behavior of MRRs built on silicon-on-insulator (SOI) platforms. These include thermo-optic, free-carrier absorption (FCA), free-carrier dispersion (FCD), two-photon absorption (TPA), and the Kerr effect. Here, we study their relative strengths in a typical SOI electron beam foundry platform. We match a constructed model with coupled-mode theory (CMT) to experimental measurements. Our results suggest that all these effects, except for the thermo-optic, play an important role in altering ultrafast dynamics.

An all-pass MRR (Fig. 1A) with nonlinearities can be modeled via a CMT method [4]. Its normalized complex amplitude,  $a$ , and normalized carrier density,  $n$ , evolve with

$$\frac{d}{dt} a = i(d\omega - n_{\text{Kerr}} j a^2 + S_{\text{fcd}} a_{\text{tpa}} n) a - (1 + a_{\text{tpa}} j a^2 + g_{\text{fca}} a_{\text{tpa}} n) a + \frac{Q}{g_p R_{\text{in}}(t)} \quad (1a)$$

$$\frac{d}{dt} n = j a^4 - n \tau; \quad (1b)$$

where  $d\omega$